

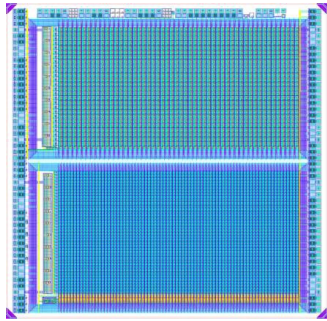


DRD3 Week Jun. 24 / WG1

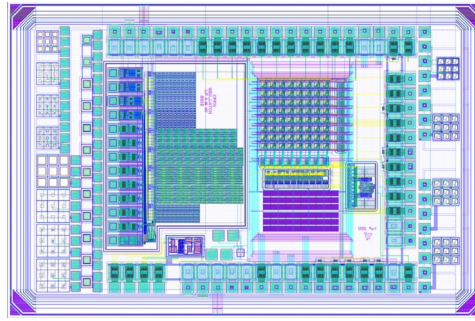
# Characterization of the RD50-MPW4 HV-CMOS pixel sensor

**Bernhard Pisl (HEPHY), Harald Handerkas (HEPHY)**  
on behalf of the (former) CERN RD50 CMOS working group

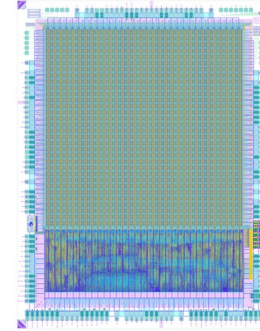
# RD50 DMAPS Series



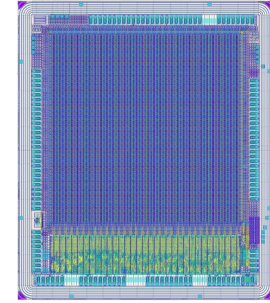
RD50-MPW1  
(5mm x 5mm)



RD50-MPW2  
(3.2mm x 2.1mm)



RD50-MPW3  
(5.1mm x 6.6mm)



RD50-MPW4  
(5.4mm x 6.3mm)

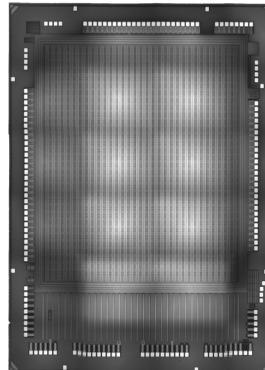
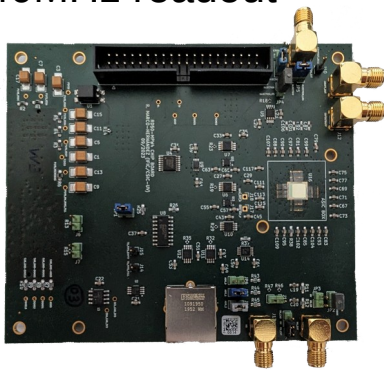


- HV-CMOS sensors fabricated in *LFoundry* 150nm process
- **Goals:** Evaluation of technology for
  - Radiation hardness
  - High granularity
  - Timing performance

## RD50-MPW3 / -MPW4

### Both sensors feature:

- 64x64 pixel matrix arranged in 32 FEI-3 style double columns
- Active area of 4x4mm<sup>2</sup>
- Pixel-size of 62x62μm<sup>2</sup>
- 8 bit timestamp information (based on 25ns) for each hit
- 4 bit in-pixel trimming
- 640MHz readout

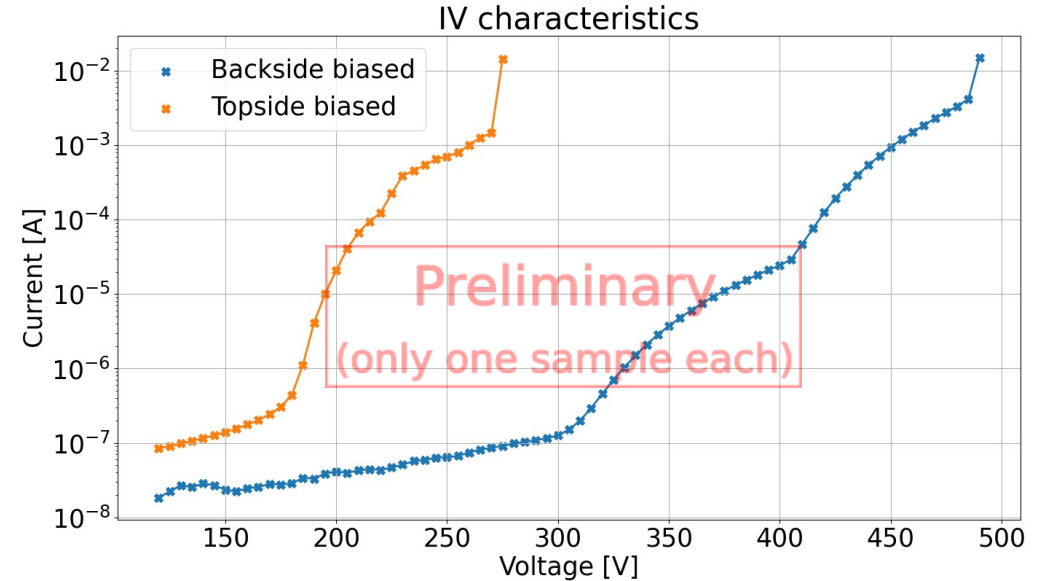


### Modifications / Improvements MPW3 → MPW4

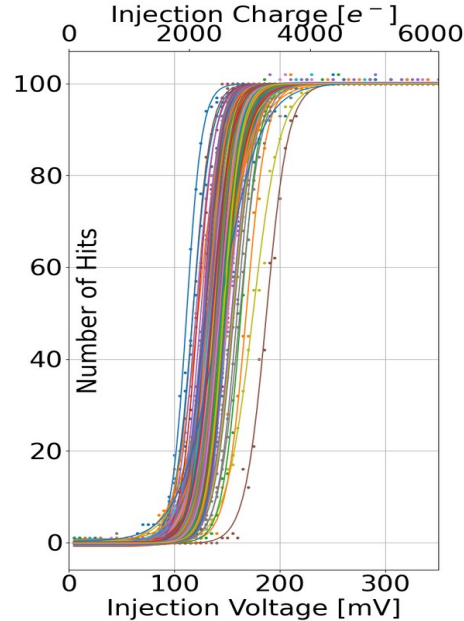
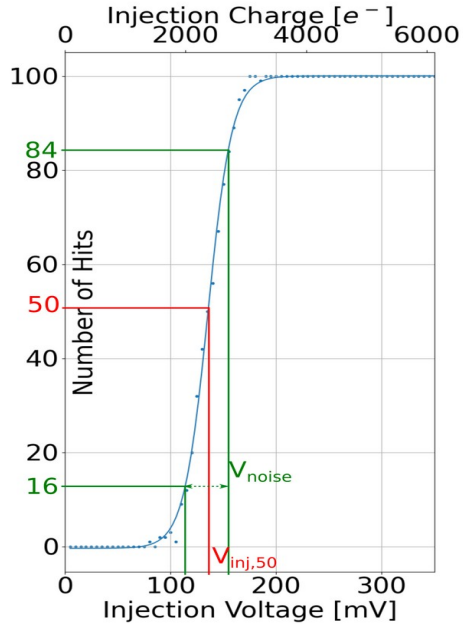
- Noise significantly reduced by
  - separating power domains of in-pixel and peripheral digital readout
  - improved routing of power lines
- Optimized guard rings
  - higher breakdown → improved radiation hardness
- Backside processing
  - higher breakdown → improved radiation hardness
- Length of EOC readout signals adjustable

## IV measurements

- IV measurements of whole chip
- Breakdown at:
  - **Topside biased**  $V \approx 270V$
  - **Backside biased**  $V \approx 490V$
- Current increase for topside biased already at  $V \approx 190V$ 
  - Full depletion reached
  - Depletion region touches back or sides of the sensor



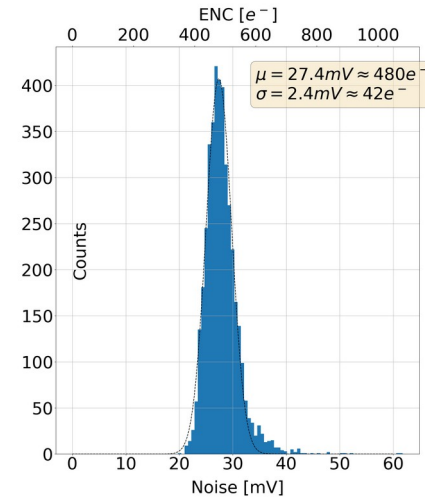
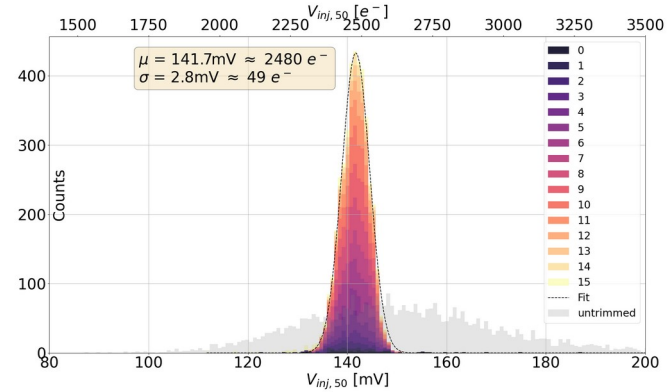
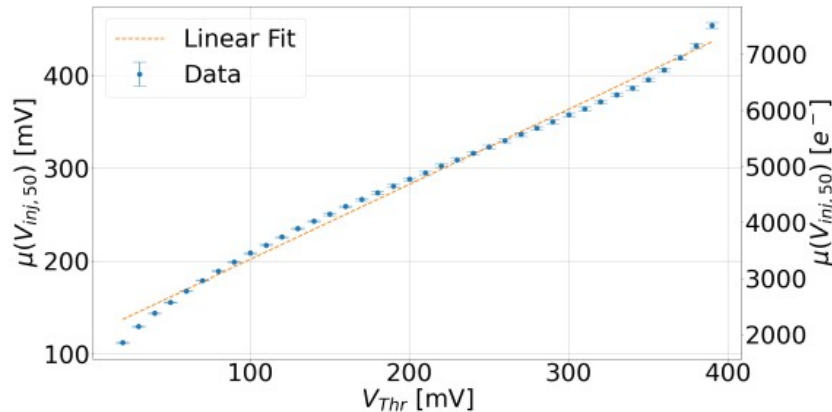
## Injection Scan methods



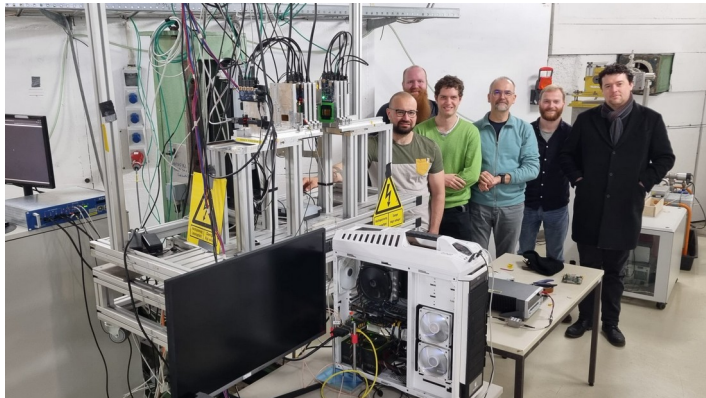
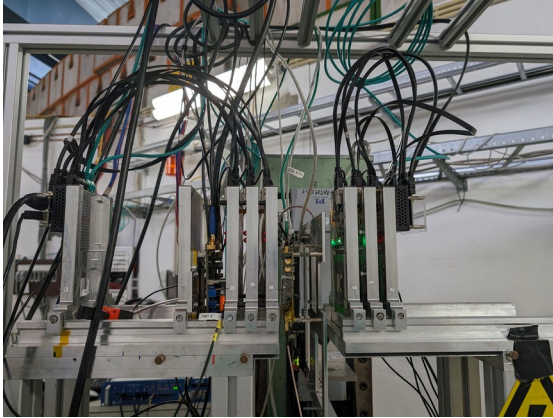
- Utilizing In-Pixel injection capacity of  $C \approx 2.8\text{fF}$
- Inject 100 times for  $V_{inj}$  from  $0 \rightarrow 350\text{mV}$  in  $5\text{mV}$  steps for full matrix
- Record and fit data to S-curve
- $V_{inj,50}$  : voltage at which 50% of injected hits detected
- $V_{noise}$  : voltage difference from 16%  $\rightarrow$  84% of injected hits detected

# Injection Scan results

- After trimming pixel response  $\sigma \approx 50e^-$
- Equivalent Noise Charge:  $480(\pm 42)e^-$
- Scanning threshold voltage  $\rightarrow$  convert threshold voltage to charge
  - CSA (+ comparator) show linear behavior for wide range of  $V_{Thr}$  and  $V_{Inj}$



## Testbeam Setup

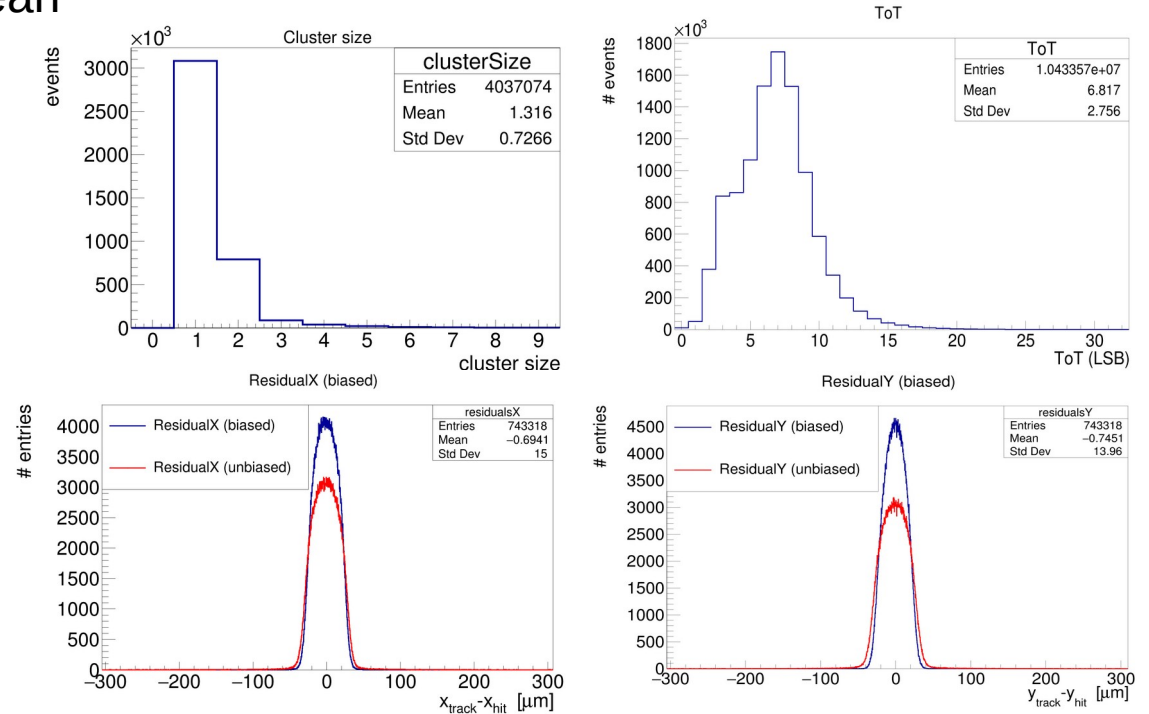


- Test-Beam at DESY in Apr. 2024
- Focus on non-irradiated samples / comparison of top- and backside biasing
- 4.2 GeV electrons at  $f \approx 10\text{kHz}$
- *Adenium* (Alpide based) telescope
- *AIDA 2020 TLU* for synchronization
- *Telepix* as ROI trigger and timing layer



## General Testbeam Results

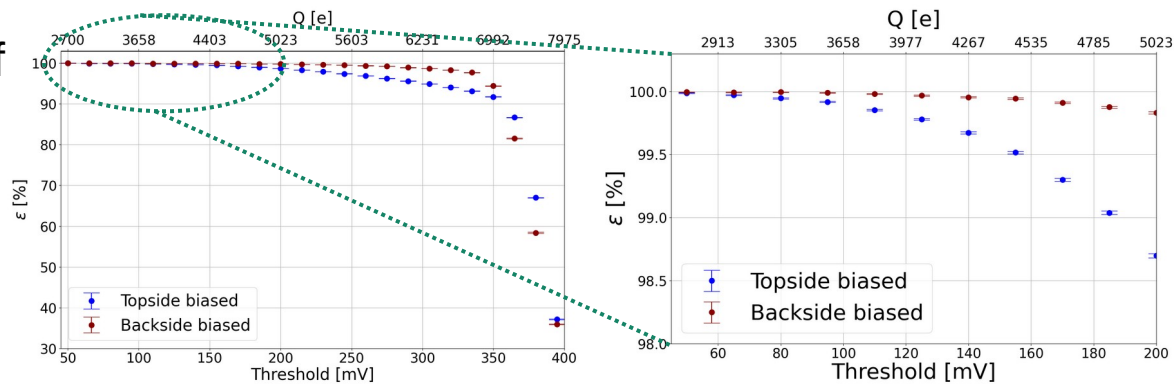
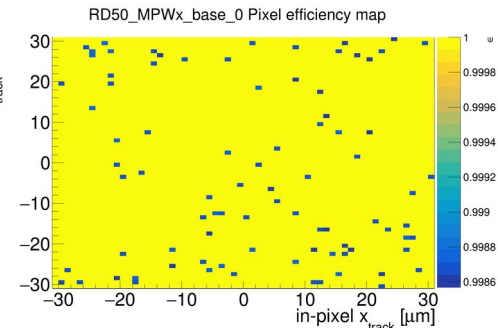
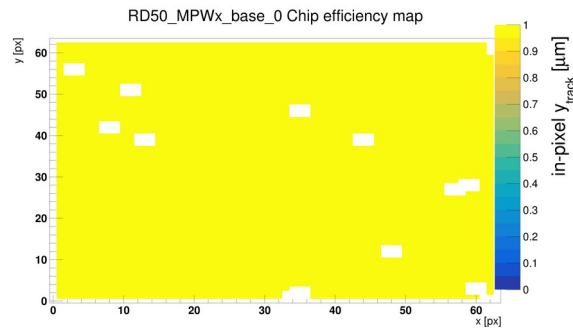
- Average cluster size  $\approx 1.3$
- Average Time over Threshold  $\approx 6.8\text{LSB}$
- Spatial resolution by geometric mean of  $\sigma$  of the residuals (biased and unbiased):
  - Resolution in X  $\approx 17.8\mu\text{m}$
  - Resolution in Y  $\approx 16.4\mu\text{m}$
  - Difference most likely due to rectangular *Alpide* pixels





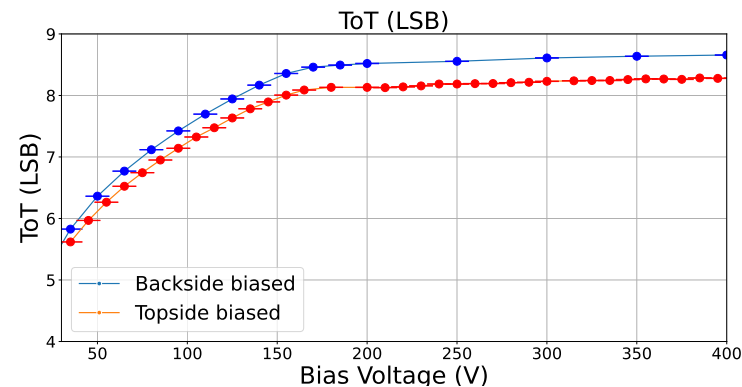
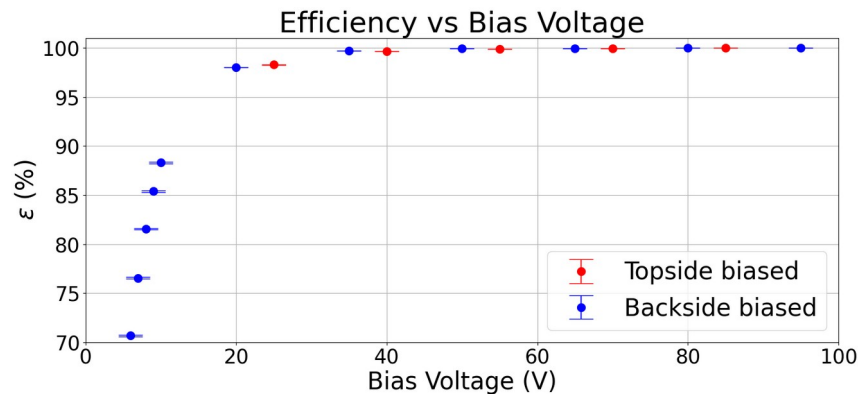
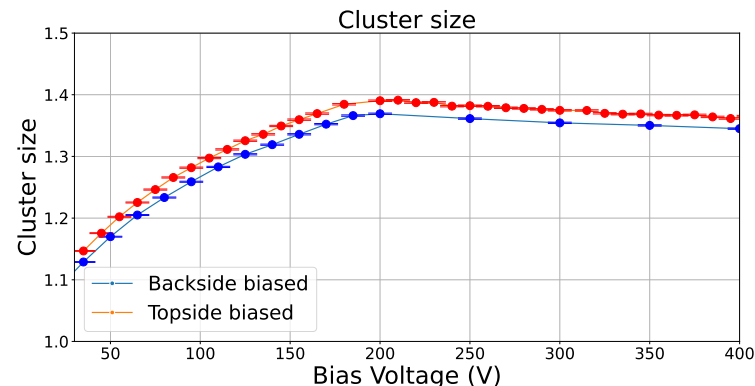
# Efficiency

- Total efficiency > 99.99% evaluated
  - $V_{Bias} = -190V$
  - $Q_{Thr} \approx 2700e^-$
- Homogeneous in-pixel efficiency
- Efficiency >99% up to threshold of  $O(5000e^-)$ 
  - Backside biased sample working better at high thresholds (compared to topside biasing)



## Bias Voltage scan

- Cluster size and ToT show saturation at  $V_{\text{Bias}} \approx 200\text{V}$ 
  - Full depletion reached
- Efficiency  $> 97\%$  down to  $V_{\text{Bias}} \approx 20\text{V}$



## Summary / Outlook

- RD50-MPW4 fixed problems of MPW3
- Backside processing allows for higher bias voltages as well as threshold settings
- Beam campaign with irradiated samples planned in autumn 2024 at *DESY*
  - Samples irradiated from  $1 \times 10^{14} \rightarrow 3 \times 10^{16}$  1MeV  $n_{eq}/cm^2$
- RD50-MPW series is a success story and ready for optimization towards
  - Larger matrix
  - Improved spatial and time resolution
  - Reduce power consumption
- For more detailed ideas follow Eva's talk



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# Thank you for your attention! Questions?

This work has been partly performed in the framework of the CERN-RD50 collaboration.

The measurements leading to these results have been performed at the Test Beam Facility at DESY Hamburg (Germany), a member of the Helmholtz Association (HGF).

The research leading to these results has received funding from the European Union's Horizon Europe research and innovation programme under grant agreement no. 101057511.



# BACKUP

## Recap MPW3

- Noise coupling from digital periphery into analog matrix
  - Only top half of matrix usable
  - Thresholds  $> 5000e^-$  necessary
- Total efficiency of  $\sim 97\%$  evaluated
  - Strong corner effects (efficiency drop to  $\sim 80\%$ ) observed

